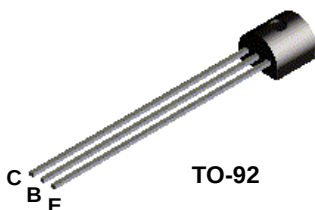


2N4125



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents of 10 μ A to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4125	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier
(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ }\mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$	4.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$		50	nA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		50	nA

ON CHARACTERISTICS*

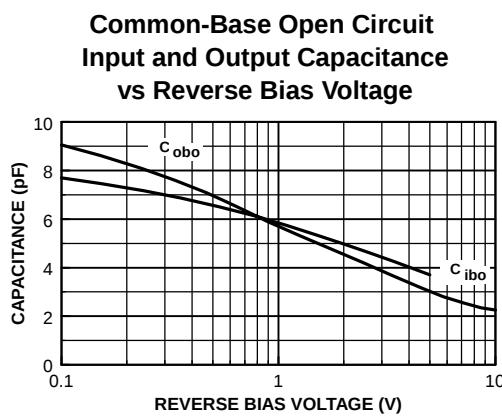
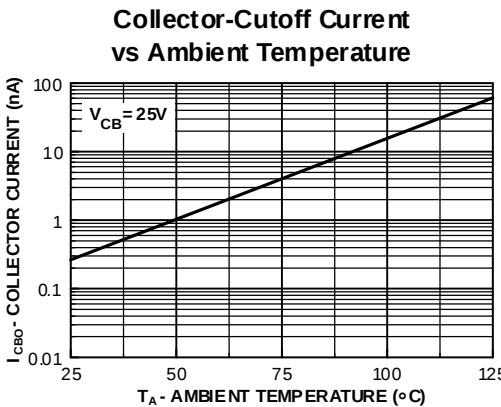
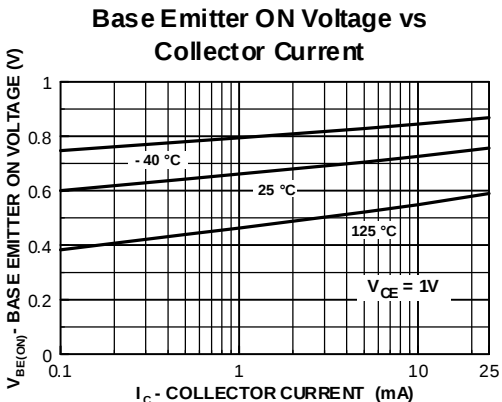
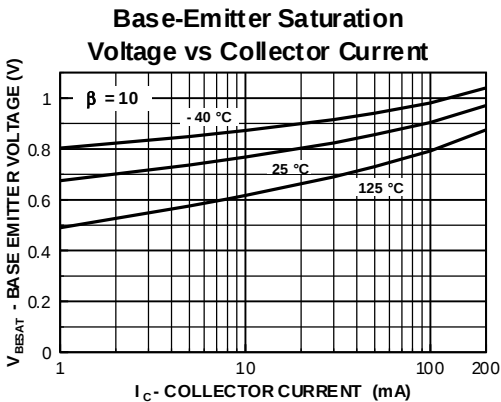
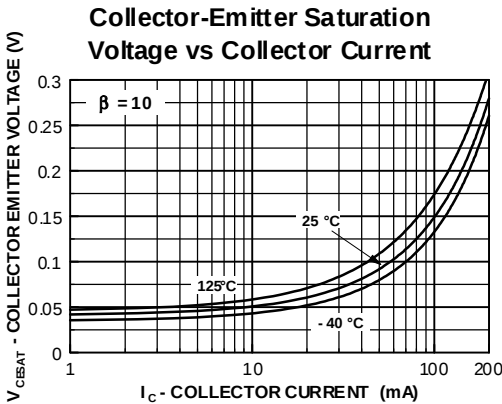
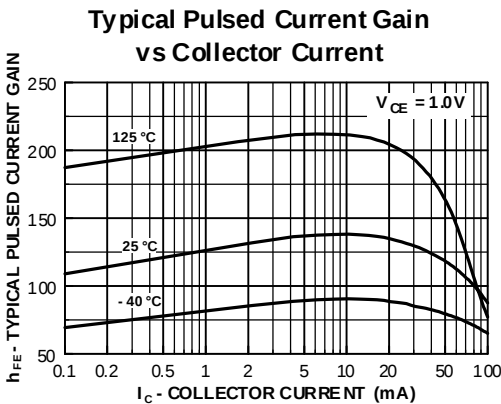
h_{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$	50 25	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.95	V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 100 \text{ kHz}$		4.5	pF
C_{ib}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, f = 100 \text{ kHz}$		10	pF
h_{fe}	Small-Signal Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$	50 2.0	200	
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ }\mu\text{A},$ $R_S = 1.0 \text{ k}\Omega,$ $f = 10\text{Hz to } 15.7 \text{ kHz},$		5.0	dB

*Pulse Test: Pulse Width $\leq 300 \text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

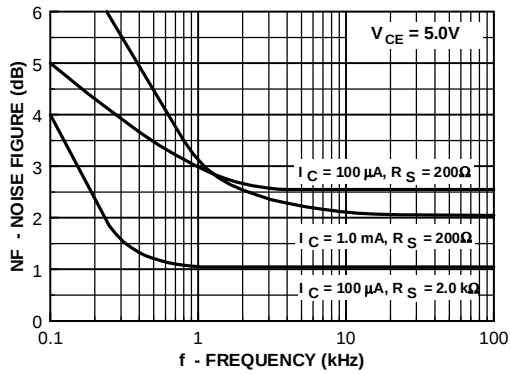


PNP General Purpose Amplifier

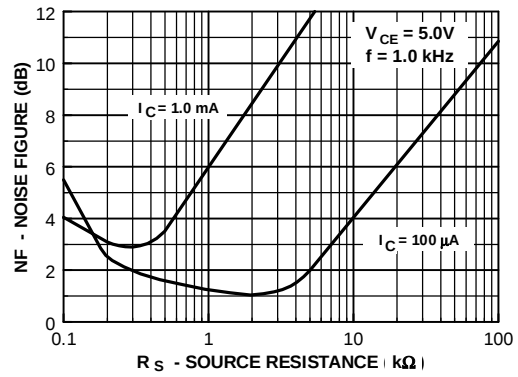
(continued)

Typical Characteristics (continued)

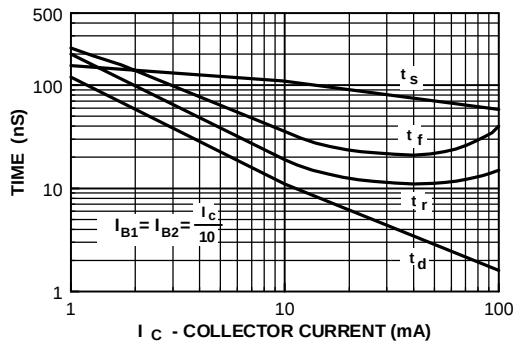
Noise Figure vs Frequency



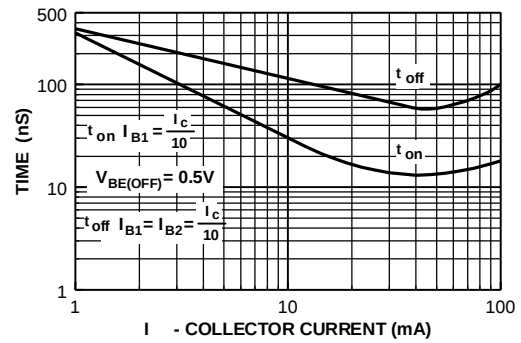
Noise Figure vs Source Resistance



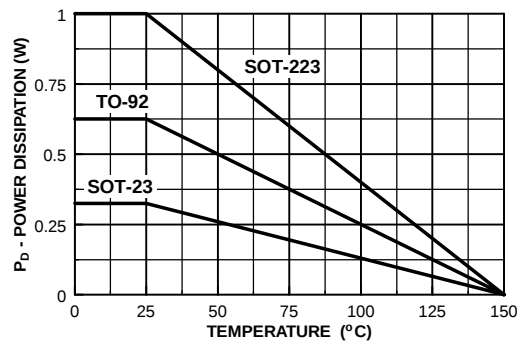
Switching Times vs Collector Current



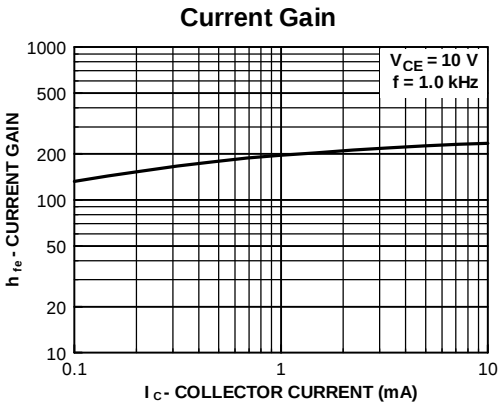
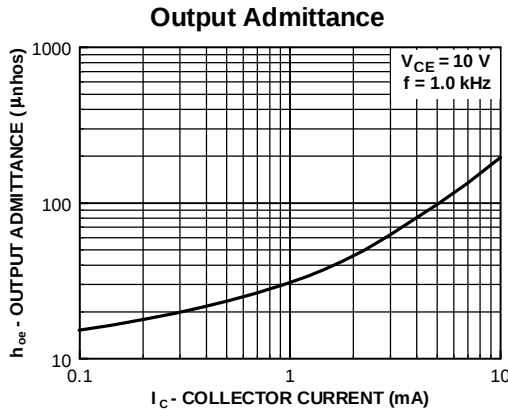
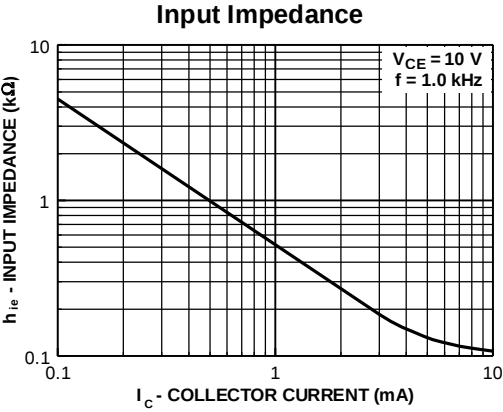
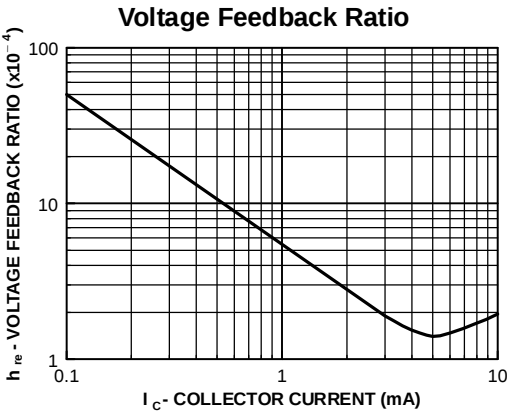
Turn On and Turn Off Times vs Collector Current



Power Dissipation vs Ambient Temperature



Typical Characteristics (continued)



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